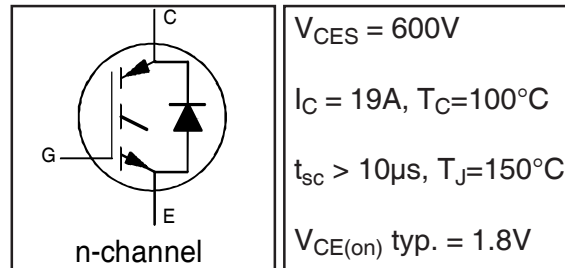


INSULATED GATE BIPOLAR TRANSISTOR WITH  
ULTRAFAST SOFT RECOVERY DIODE

IRGB10B60KDPbF  
IRGS10B60KDPbF  
IRGSL10B60KDPbF

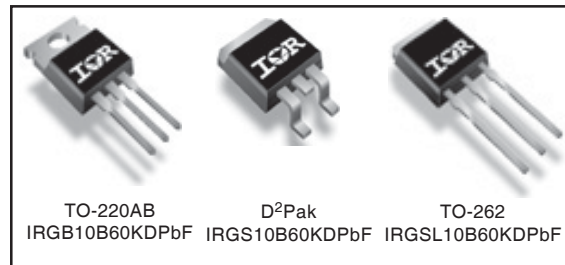
**Features**

- Low VCE (on) Non Punch Through IGBT Technology.
- Low Diode VF.
- 10µs Short Circuit Capability.
- Square RBSOA.
- Ultrasoft Diode Reverse Recovery Characteristics.
- Positive VCE (on) Temperature Coefficient.
- Lead-Free



**Benefits**

- Benchmark Efficiency for Motor Control.
- Rugged Transient Performance.
- Low EMI.
- Excellent Current Sharing in Parallel Operation.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	35	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	19	
$I_{CM}$	Pulsed Collector Current	44	
$I_{LM}$	Clamped Inductive Load Current ④	44	
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	35	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	19	
$I_{FM}$	Diode Maximum Forward Current	44	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	156	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	62	
$T_J$	Operating Junction and	-55 to +150	$^\circ C$
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	0.8	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	3.4	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount①	—	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state)②	—	—	40	
Wt	Weight	—	1.44	—	g

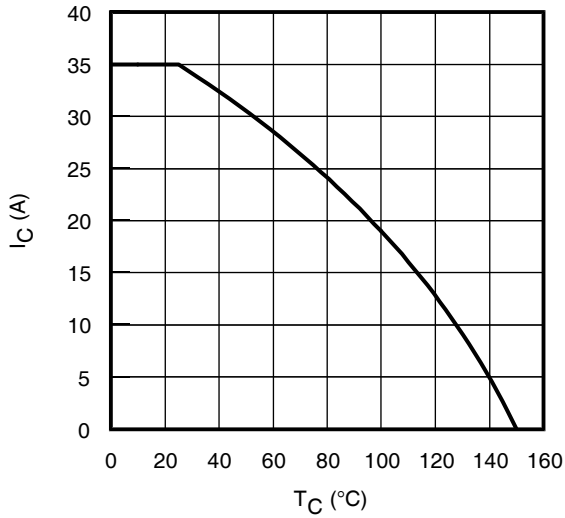
## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 500\mu A$	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.3	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA, (25^\circ\text{C}-150^\circ\text{C})$	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	1.5	1.80	2.20	V	$I_C = 10A, V_{GE} = 15V$	5, 6, 7
		—	2.20	2.50		$I_C = 10A, V_{GE} = 15V, T_J = 150^\circ\text{C}$	9, 10, 11
$V_{GE(th)}$	Gate Threshold Voltage	3.5	4.5	5.5	V	$V_{CE} = V_{GE}, I_C = 250\mu A$	9, 10, 11
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	$V_{CE} = V_{GE}, I_C = 1.0mA, (25^\circ\text{C}-150^\circ\text{C})$	12
$g_{fe}$	Forward Transconductance	—	7.0	—	S	$V_{CE} = 50V, I_C = 10A, PW=80\mu s$	
$I_{CES}$	Zero Gate Voltage Collector Current	—	3.0	150	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$	
		—	300	700		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$	
$V_{FM}$	Diode Forward Voltage Drop	—	1.30	1.45	V	$I_C = 10A$	8
		—	1.30	1.45		$I_C = 10A, T_J = 150^\circ\text{C}$	
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$	

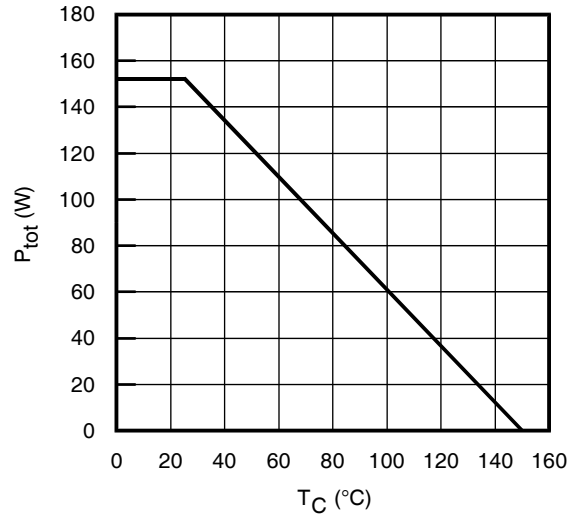
## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
$Q_g$	Total Gate Charge (turn-on)	—	38	—	nC	$I_C = 10A$	CT1
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	4.3	—		$V_{CC} = 400V$	
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	16.3	—		$V_{GE} = 15V$	
$E_{on}$	Turn-On Switching Loss	—	140	247	$\mu J$	$I_C = 10A, V_{CC} = 400V$	CT4
$E_{off}$	Turn-Off Switching Loss	—	250	360		$V_{GE} = 15V, R_G = 47\Omega, L = 200\mu H$	
$E_{tot}$	Total Switching Loss	—	390	607		$L_s = 150nH, T_J = 25^\circ\text{C}$ ③	
$t_{d(on)}$	Turn-On Delay Time	—	30	39	ns	$I_C = 10A, V_{CC} = 400V$	CT4
$t_r$	Rise Time	—	20	29		$V_{GE} = 15V, R_G = 47\Omega, L = 200\mu H$	
$t_{d(off)}$	Turn-Off Delay Time	—	230	262		$L_s = 150nH, T_J = 25^\circ\text{C}$	
$t_f$	Fall Time	—	23	32			
$E_{on}$	Turn-On Switching Loss	—	230	340	$\mu J$	$I_C = 10A, V_{CC} = 400V$	CT4
$E_{off}$	Turn-Off Switching Loss	—	350	464		$V_{GE} = 15V, R_G = 47\Omega, L = 200\mu H$	
$E_{tot}$	Total Switching Loss	—	580	804		$L_s = 150nH, T_J = 150^\circ\text{C}$ ③	
$t_{d(on)}$	Turn-On Delay Time	—	30	39	ns	$I_C = 10A, V_{CC} = 400V$	14, 16
$t_r$	Rise Time	—	20	28		$V_{GE} = 15V, R_G = 47\Omega, L = 200\mu H$	
$t_{d(off)}$	Turn-Off Delay Time	—	250	274		$L_s = 150nH, T_J = 150^\circ\text{C}$	
$t_f$	Fall Time	—	26	34			
$C_{ies}$	Input Capacitance	—	620	—	pF	$V_{GE} = 0V$	
$C_{oes}$	Output Capacitance	—	62	—		$V_{CC} = 30V$	
$C_{res}$	Reverse Transfer Capacitance	—	22	—		$f = 1.0MHz$	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 150^\circ\text{C}, I_C = 44A, V_p = 600V$ $V_{CC} = 500V, V_{GE} = +15V \text{ to } 0V, R_G = 47\Omega$	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	$\mu s$	$T_J = 150^\circ\text{C}, V_p = 600V, R_G = 47\Omega$ $V_{CC} = 360V, V_{GE} = +15V \text{ to } 0V$	CT3 WF4
$E_{rec}$	Reverse Recovery energy of the diode	—	245	330	$\mu J$	$T_J = 150^\circ\text{C}$	17, 18, 19
$t_{rr}$	Diode Reverse Recovery time	—	90	105	ns	$V_{CC} = 400V, I_F = 10A, L = 200\mu H$	20, 21
$I_{rr}$	Diode Peak Reverse Recovery Current	—	19	22	A	$V_{GE} = 15V, R_G = 47\Omega, L_s = 150nH$	CT4, WF3

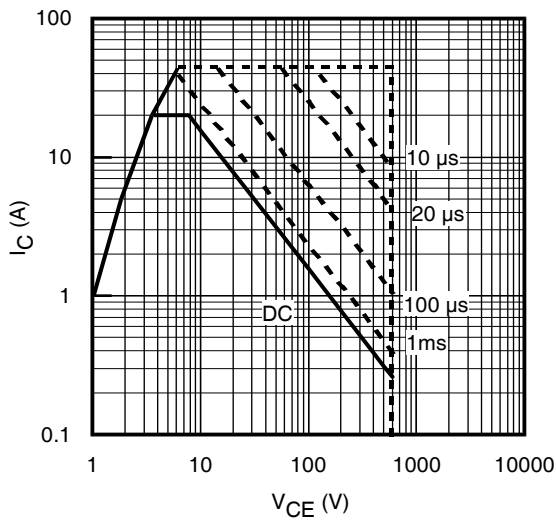
Note ① to ④ are on page 15



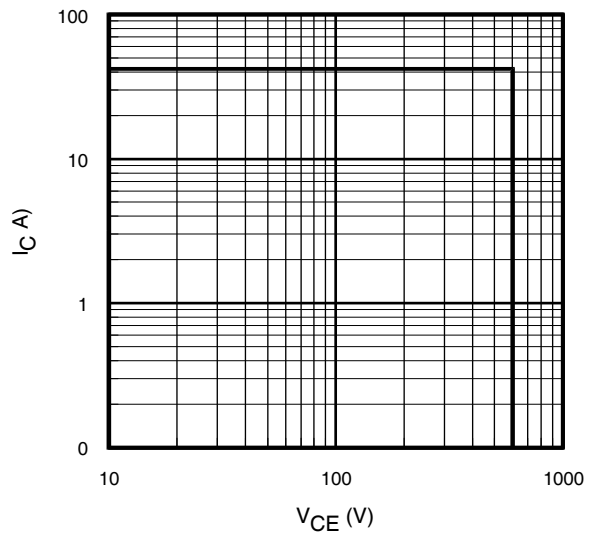
**Fig. 1** - Maximum DC Collector Current vs. Case Temperature



**Fig. 2** - Power Dissipation vs. Case Temperature

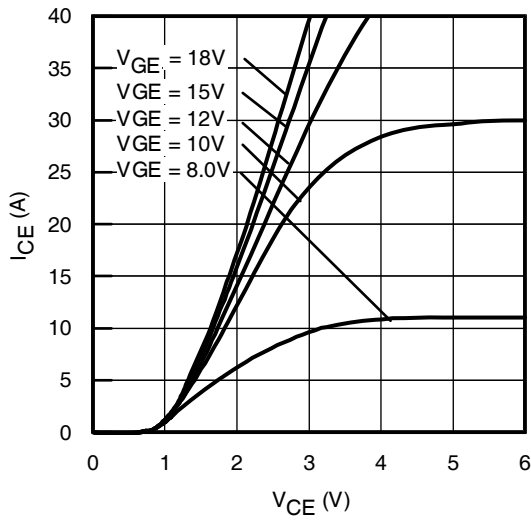


**Fig. 3** - Forward SOA  
 $T_C = 25^\circ\text{C}$ ;  $T_J \leq 150^\circ\text{C}$

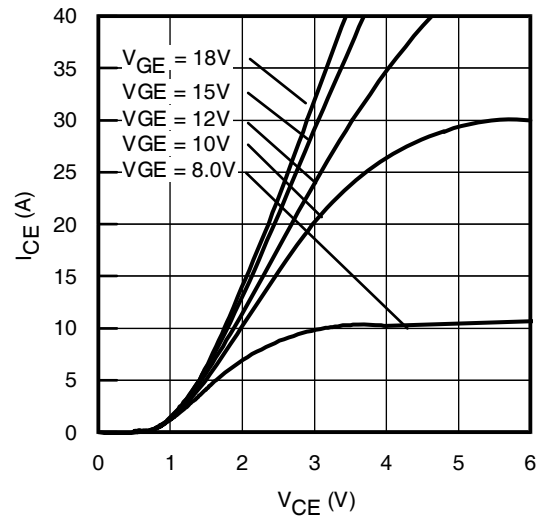


**Fig. 4** - Reverse Bias SOA  
 $T_J = 150^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$

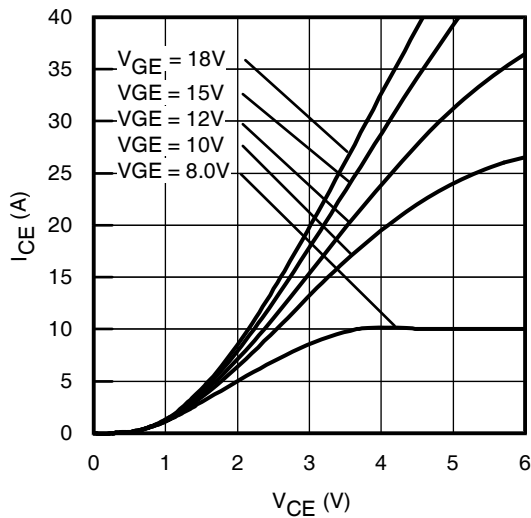
# IRG/B/S/SL10B60KDPbF



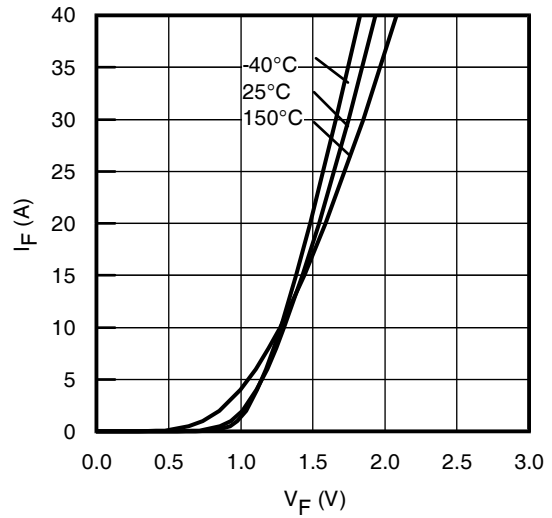
**Fig. 5** - Typ. IGBT Output Characteristics  
 $T_J = -40^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



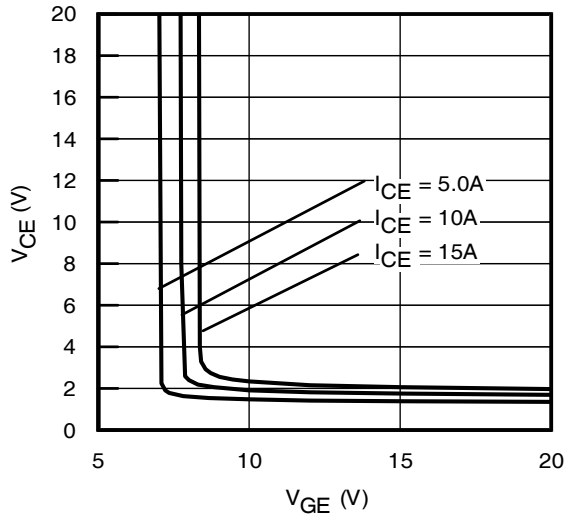
**Fig. 6** - Typ. IGBT Output Characteristics  
 $T_J = 25^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



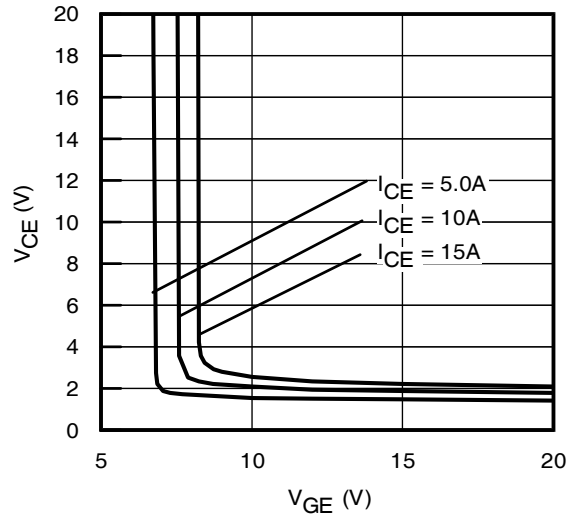
**Fig. 7** - Typ. IGBT Output Characteristics  
 $T_J = 150^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



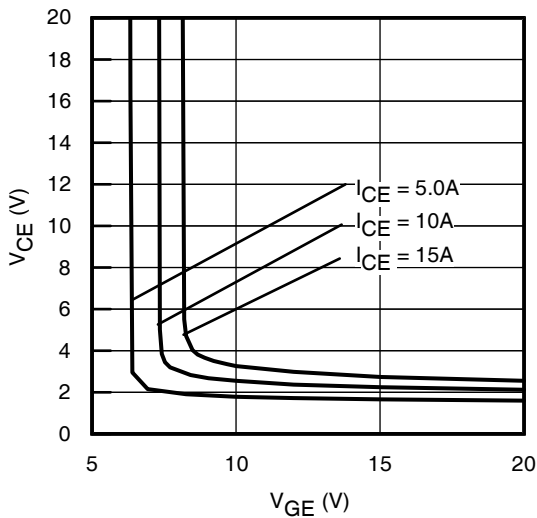
**Fig. 8** - Typ. Diode Forward Characteristics  
 $t_p = 80\mu\text{s}$



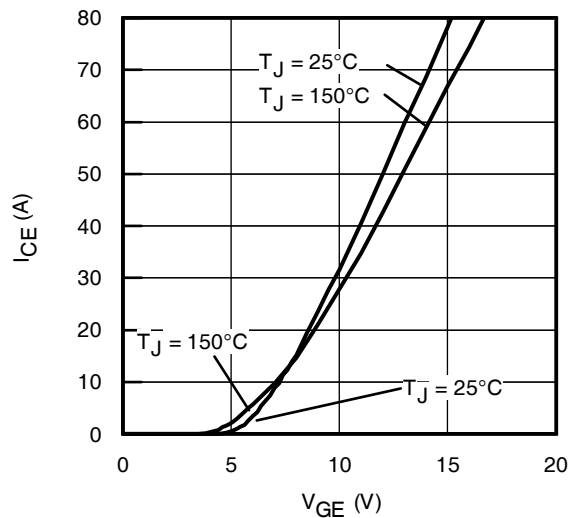
**Fig. 9** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = -40^\circ\text{C}$



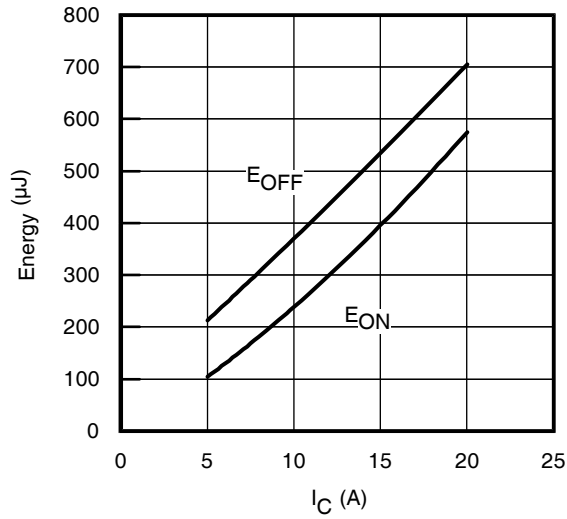
**Fig. 10** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 25^\circ\text{C}$



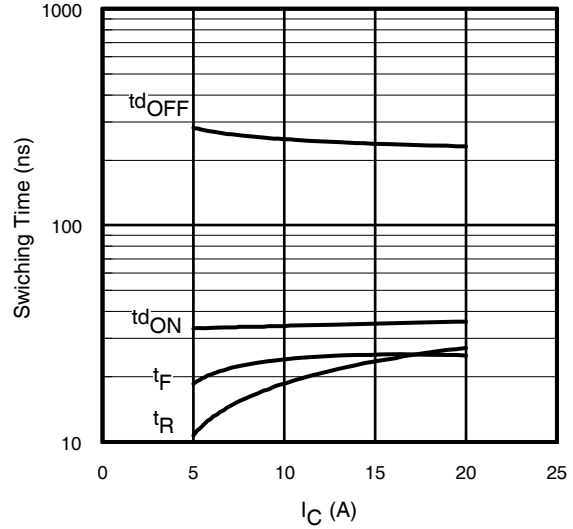
**Fig. 11** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 150^\circ\text{C}$



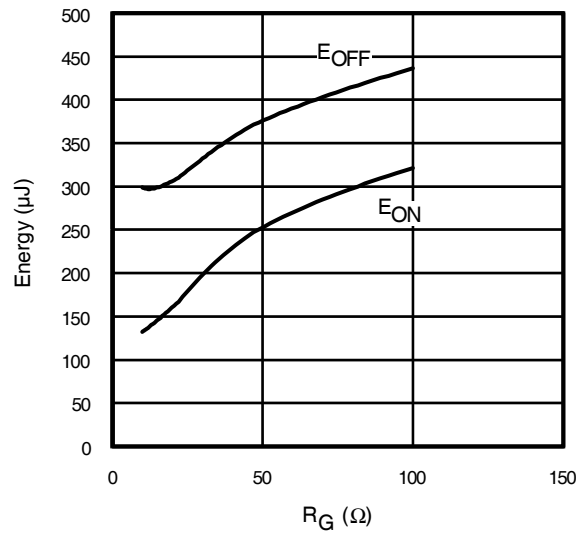
**Fig. 12** - Typ. Transfer Characteristics  
 $V_{CE} = 50\text{V}$ ;  $t_p = 10\mu\text{s}$



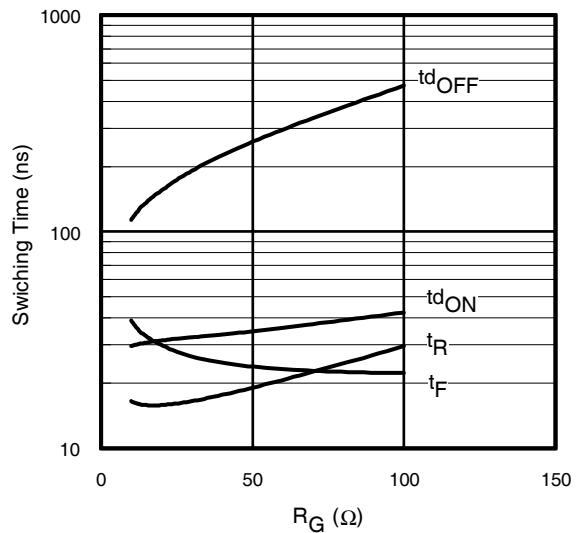
**Fig. 13** - Typ. Energy Loss vs.  $I_C$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $R_G= 47\Omega$ ;  $V_{GE}= 15\text{V}$



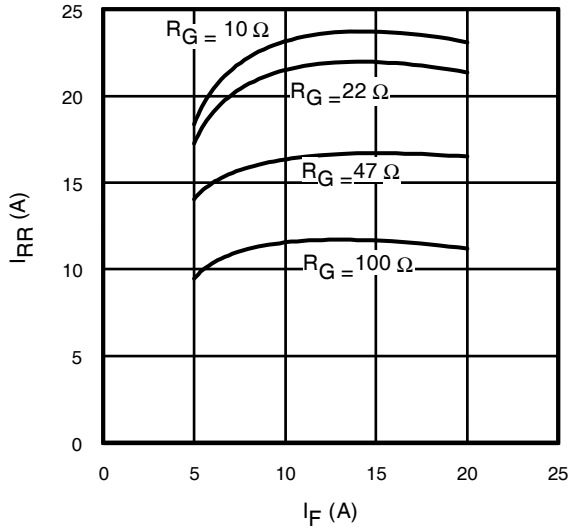
**Fig. 14** - Typ. Switching Time vs.  $I_C$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $R_G= 47\Omega$ ;  $V_{GE}= 15\text{V}$



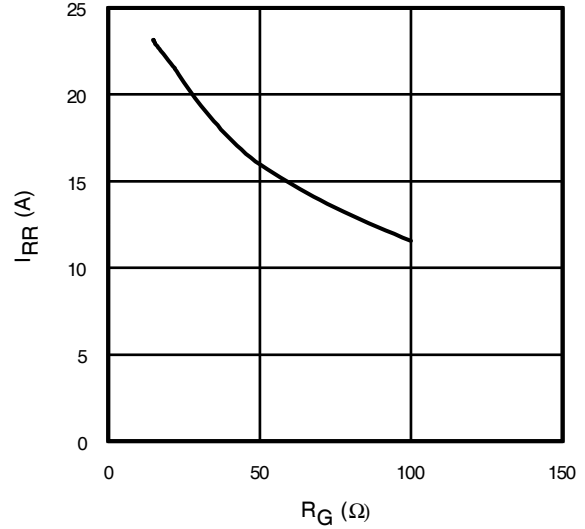
**Fig. 15** - Typ. Energy Loss vs.  $R_G$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $I_{CE}= 10\text{A}$ ;  $V_{GE}= 15\text{V}$



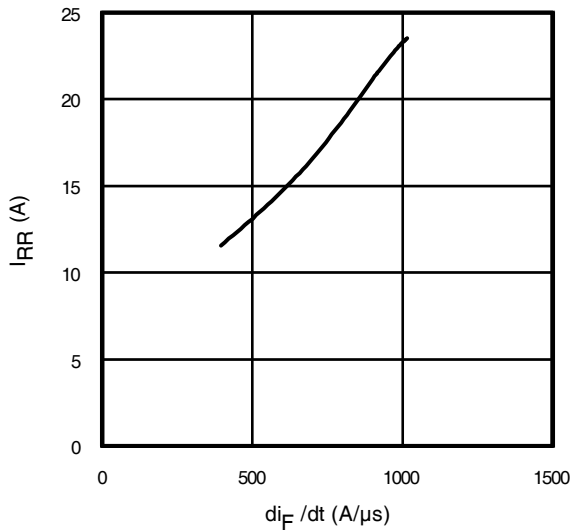
**Fig. 16** - Typ. Switching Time vs.  $R_G$   
 $T_J = 150^\circ\text{C}$ ;  $L=200\mu\text{H}$ ;  $V_{CE}= 400\text{V}$   
 $I_{CE}= 10\text{A}$ ;  $V_{GE}= 15\text{V}$



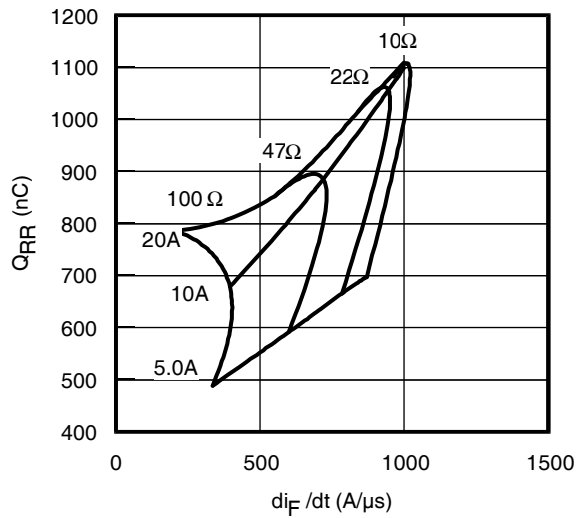
**Fig. 17** - Typical Diode  $I_{RR}$  vs.  $I_F$   
 $T_J = 150^\circ\text{C}$



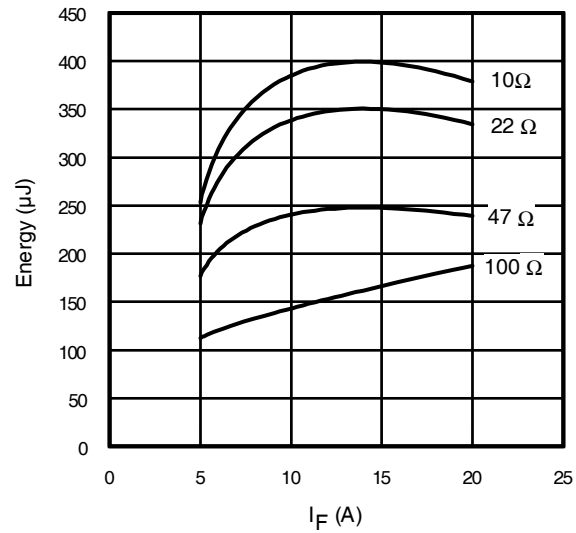
**Fig. 18** - Typical Diode  $I_{RR}$  vs.  $R_G$   
 $T_J = 150^\circ\text{C}; I_F = 10\text{A}$



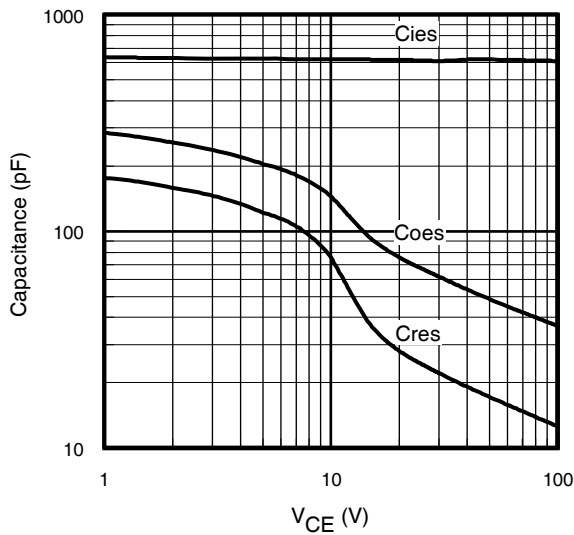
**Fig. 19** - Typical Diode  $I_{RR}$  vs.  $di_F/dt$   
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V};$   
 $I_{CE} = 10\text{A}; T_J = 150^\circ\text{C}$



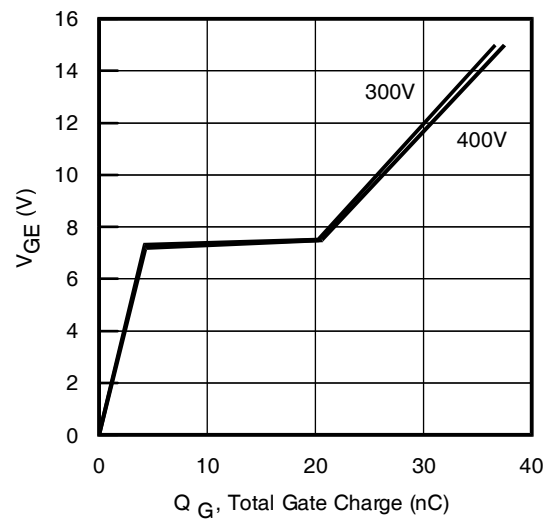
**Fig. 20** - Typical Diode  $Q_{RR}$   
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V}; T_J = 150^\circ\text{C}$



**Fig. 21** - Typical Diode  $E_{RR}$  vs.  $I_F$   
 $T_J = 150^\circ\text{C}$



**Fig. 22**- Typ. Capacitance vs.  $V_{CE}$   
 $V_{GE} = 0\text{V}$ ;  $f = 1\text{MHz}$



**Fig. 23** - Typical Gate Charge vs.  $V_{GE}$   
 $I_{CE} = 10\text{A}$ ;  $L = 600\mu\text{H}$



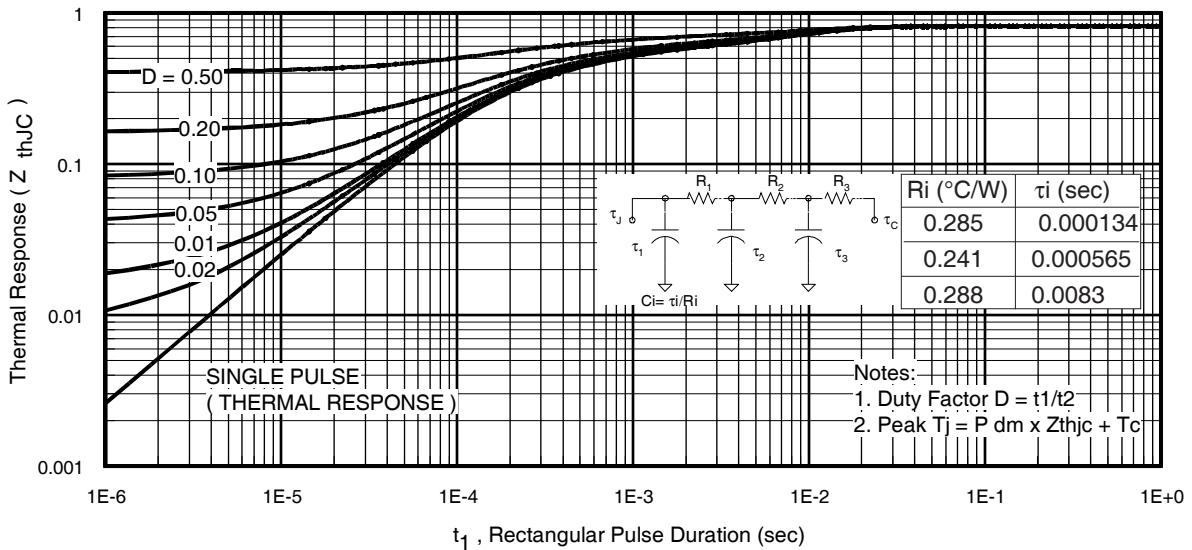


Fig 24. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

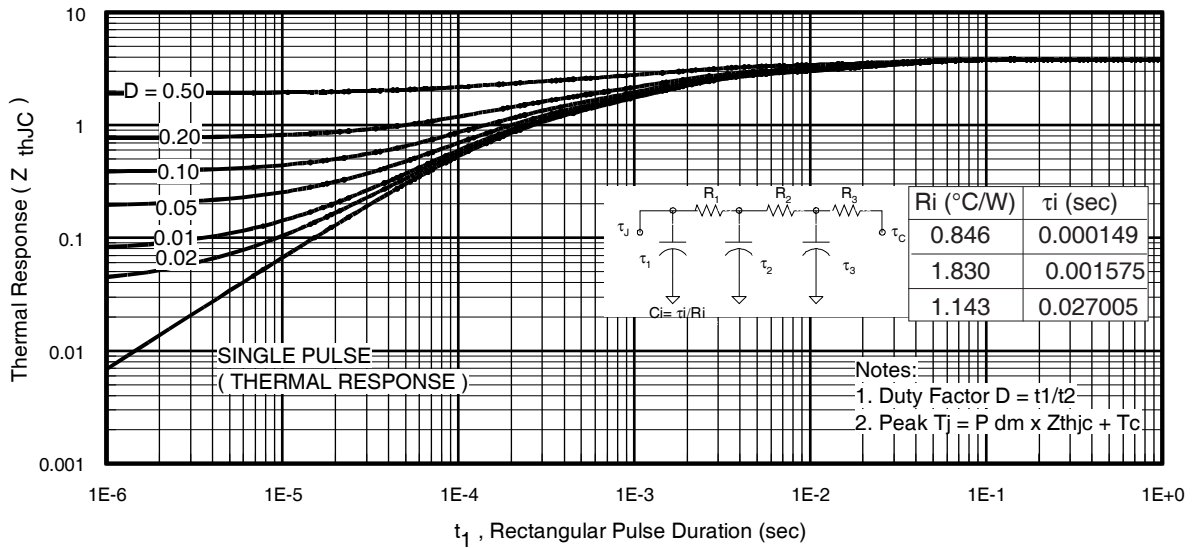
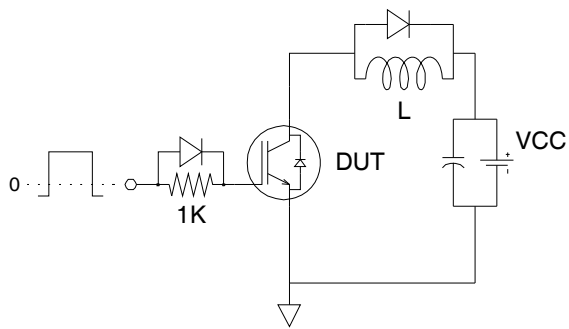


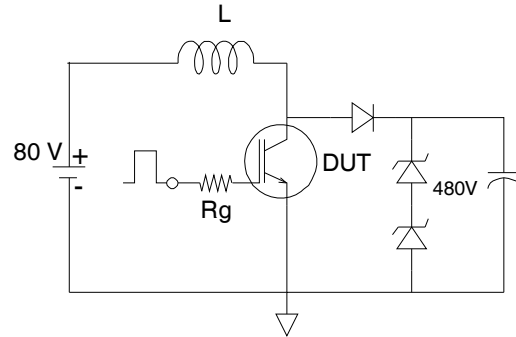
Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

# IRG/B/S/SL10B60KDPbF

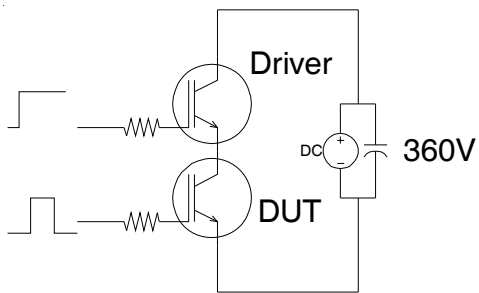
International  
**IR** Rectifier



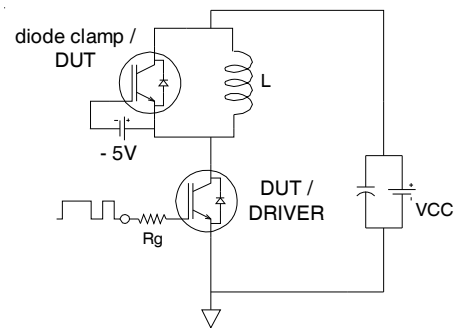
**Fig.C.T.1** - Gate Charge Circuit (turn-off)



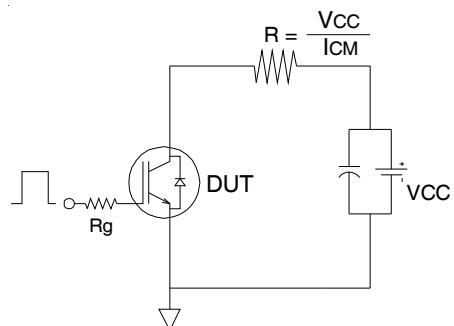
**Fig.C.T.2** - RBSOA Circuit



**Fig.C.T.3** - S.C.SOA Circuit



**Fig.C.T.4** - Switching Loss Circuit



**Fig.C.T.5** - Resistive Load Circuit

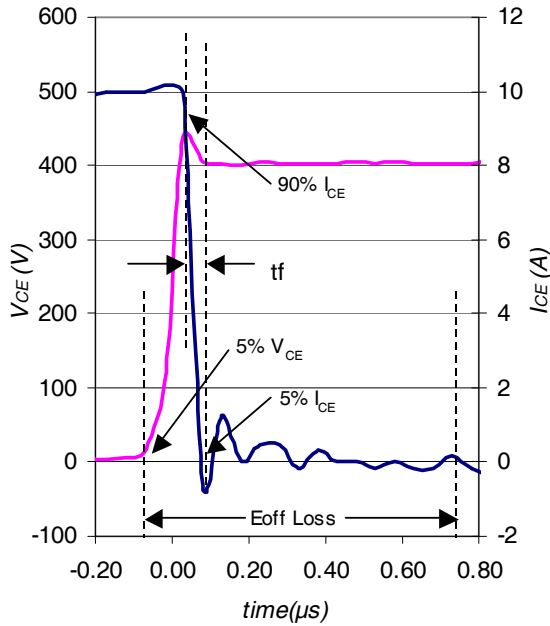


Fig. WF1- Typ. Turn-off Loss Waveform  
@  $T_J = 150^\circ\text{C}$  using Fig. CT.4

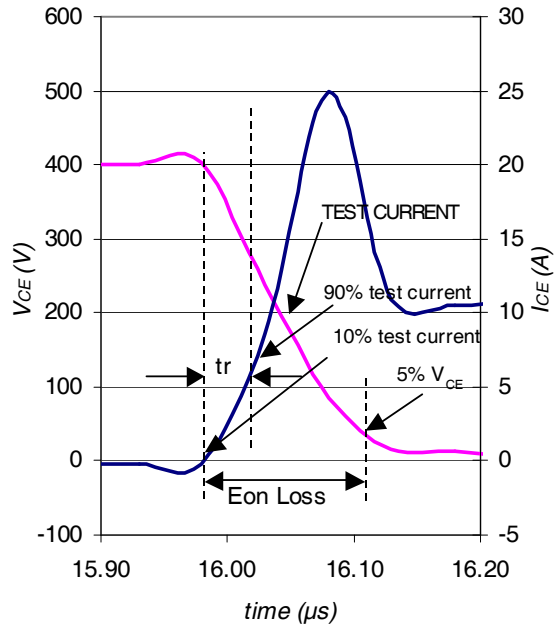


Fig. WF2- Typ. Turn-on Loss Waveform  
@  $T_J = 150^\circ\text{C}$  using Fig. CT.4

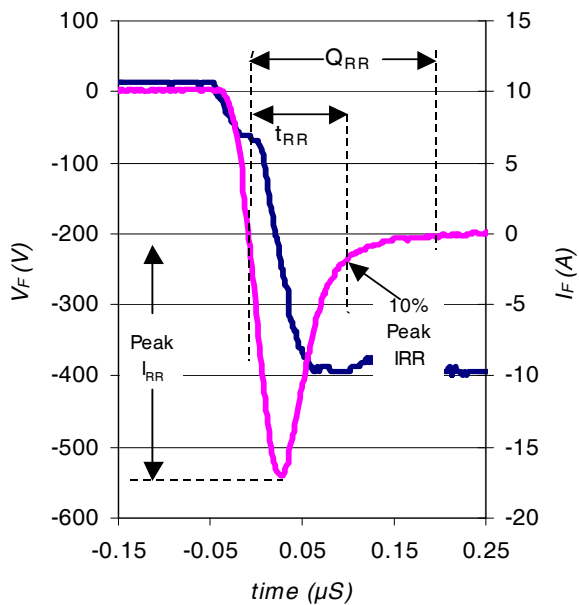


Fig. WF3- Typ. Diode Recovery Waveform  
@  $T_J = 150^\circ\text{C}$  using Fig. CT.4

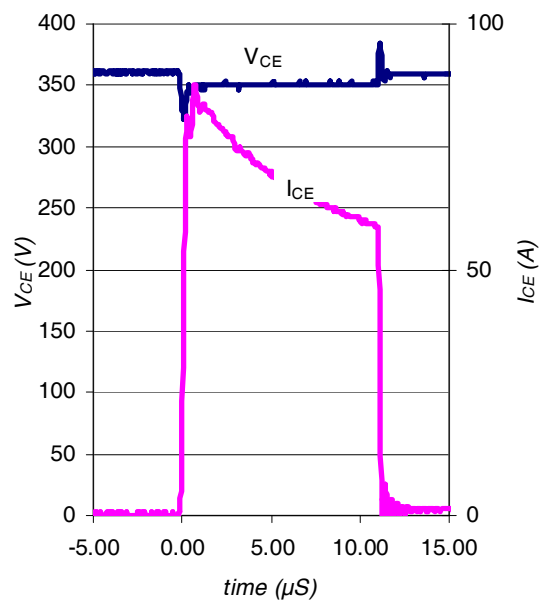
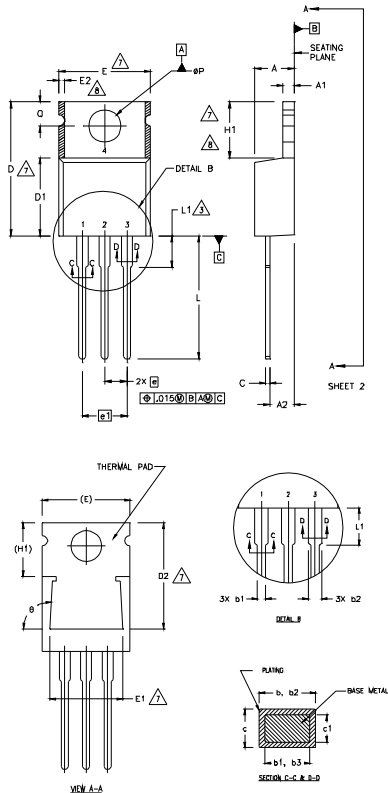


Fig. WF4- Typ. S.C Waveform  
@  $T_J = 150^\circ\text{C}$  using Fig. CT.3

# IRG/B/S/SL10B60KDPbF

## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2 DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS).
  - 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
  - 6 CONTROLLING DIMENSION : INCHES.
  - 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
  - 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs, COIPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

**DIODES**

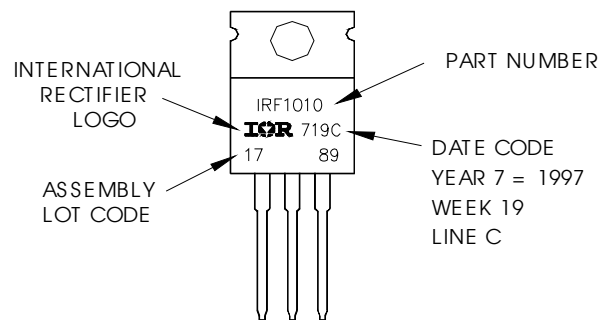
- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
ØP	3.54	4.08	.139	.161	
O	2.54	3.42	.100	.135	
φ	90°-93°		90°-93°		

## TO-220AB Part Marking Information

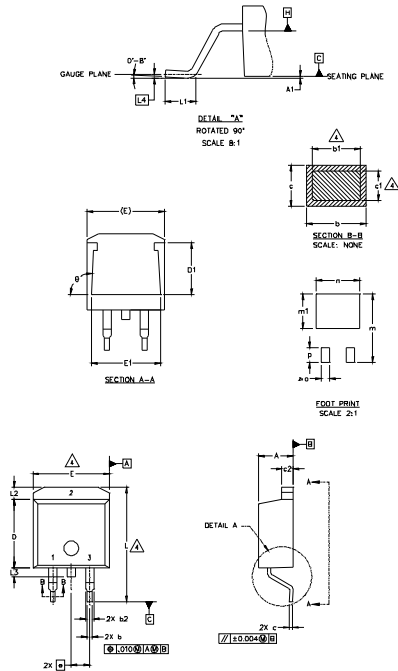
EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"

**Note:** "P" in assembly line position indicates "Lead-Free"



## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	3
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2			1.65	.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
theta	90°	93°	90°	93°	



### LEAD ASSIGNMENTS

IGBTs, CoPACK

DIODES

#### HEXFEET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

- 1.- ANODE \*
- 2.- CATHODE
- 3.- ANODE

\* PART DEPENDENT.

### NOTES:

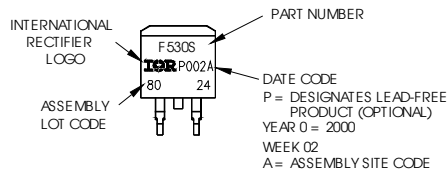
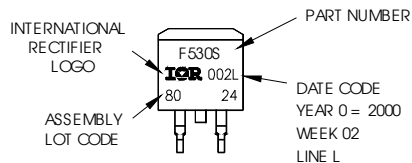
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW 02, 2000  
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line  
position indicates "Lead-Free"

OR

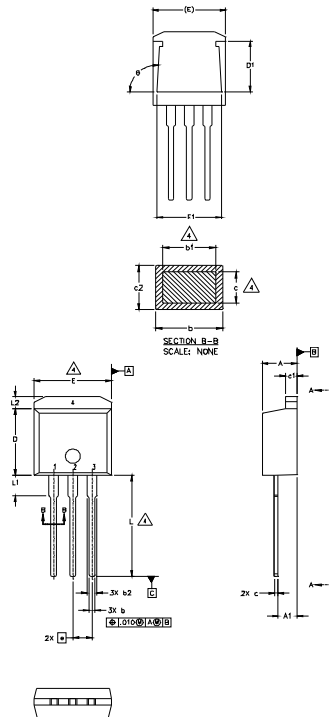


# IRG/B/S/SL10B60KDPbF

International  
**IRF** Rectifier

## TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

### LEAD ASSIGNMENTS

#### HEXFET

- 1. - GATE
- 2. - DRAIN
- 3. - SOURCE
- 4. - DRAIN

#### IGBT

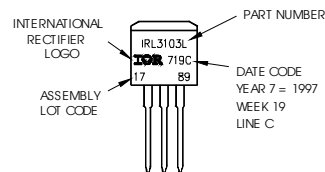
- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER

#### NOTES

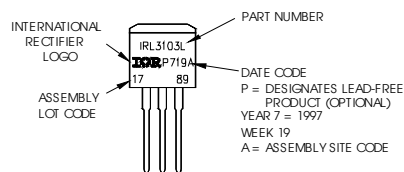
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- △ DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"  
  
Note: "P" in assembly line  
position indicates "Lead-Free"

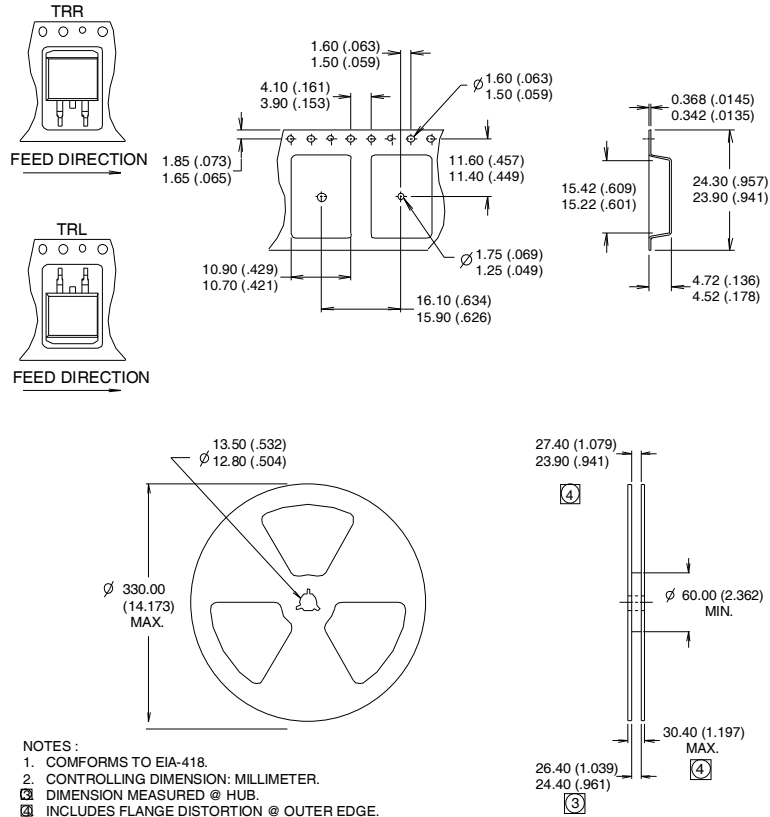


OR



## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



### Notes:

- ① This is only applied to TO-220AB package
- ② This is applied to D<sup>2</sup>Pak, when mounted on 1" square PCB ( FR-4 or G-10 Material ).  
For recommended footprint and soldering techniques refer to application note #AN-994.
- ③ Energy losses include "tail" and diode reverse recovery.
- ④  $V_{CC} = 80\% (V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 100\mu H$ ,  $R_G = 47\Omega$ .

TO-220 package is not recommended for Surface Mount Application

Data and specifications subject to change without notice.  
 This product has been designed and qualified for Industrial market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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